

**Development of 1.5 THz photon detectors
for terahertz intensity interferometry**

Speaker : Ayako Niwa

Collaborators : Hiroshi Matsuo, Hajime Ezawa, Tomohiro Koseki, Tomonori Tamura

Research background

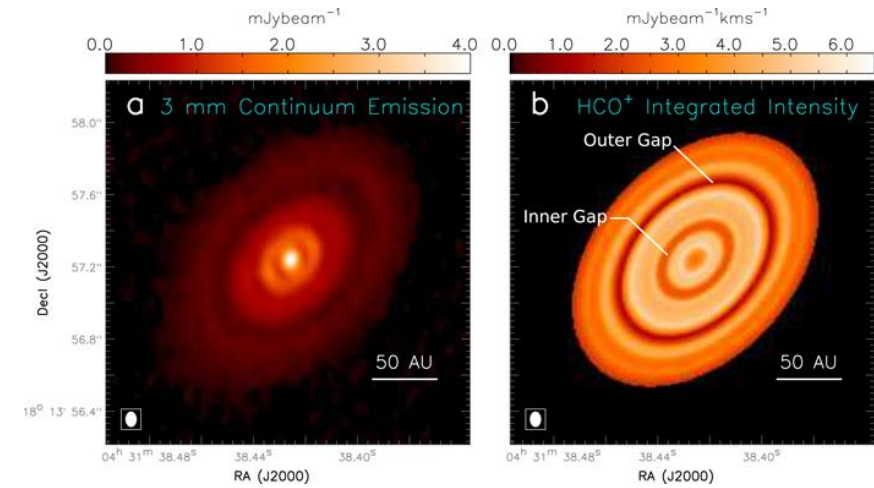
– Lack of high angular resolution instruments above 1 THz

The Observation targets for high angular resolution instruments

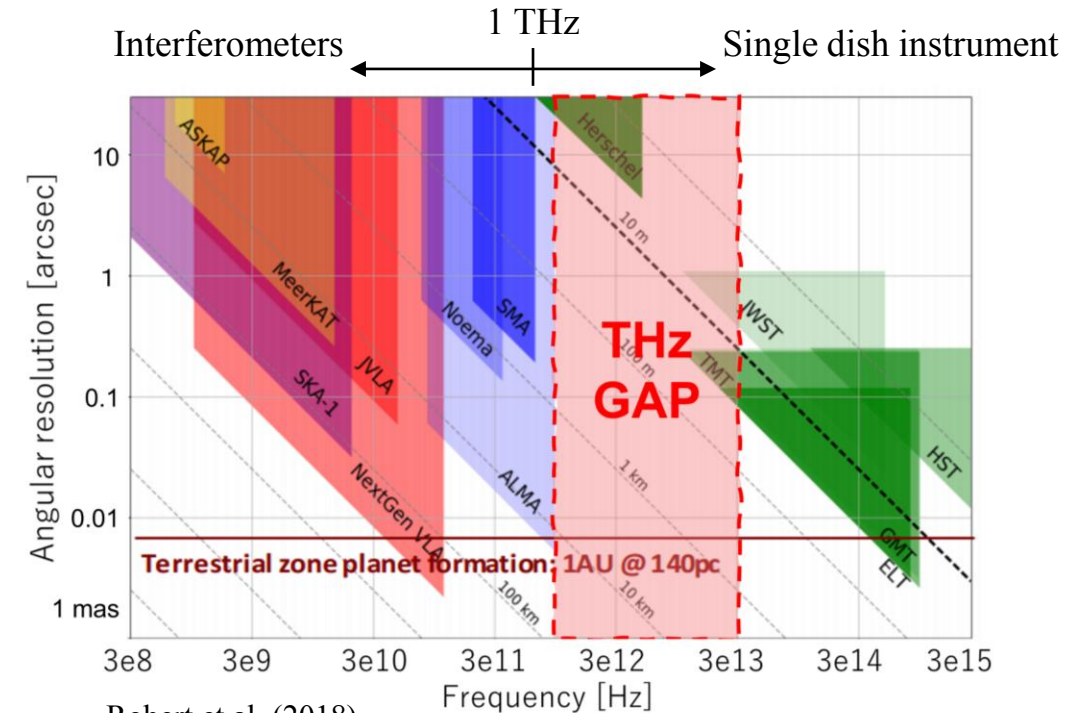
- Protoplanetary disks
- High-z galaxies
- Black holes in nearby galaxies ...etc.

Interferometers achieved high angular resolution observations at radio and terahertz regions, **except 1-30 THz region.**

We propose **Terahertz Intensity Interferometry (TII)** for the use of a space telescope.



Yen et al. (2016)



Robert et al. (2018)

Research background

– Synthesis imaging by Terahertz Intensity Interferometry

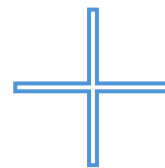
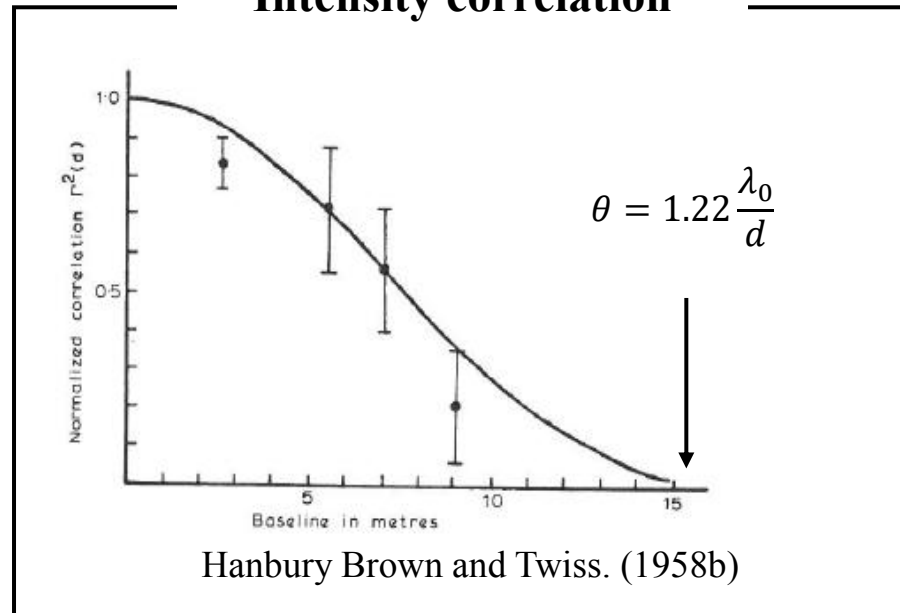
□ Terahertz Intensity Interferometry (TII)

✓ Synthesis imaging

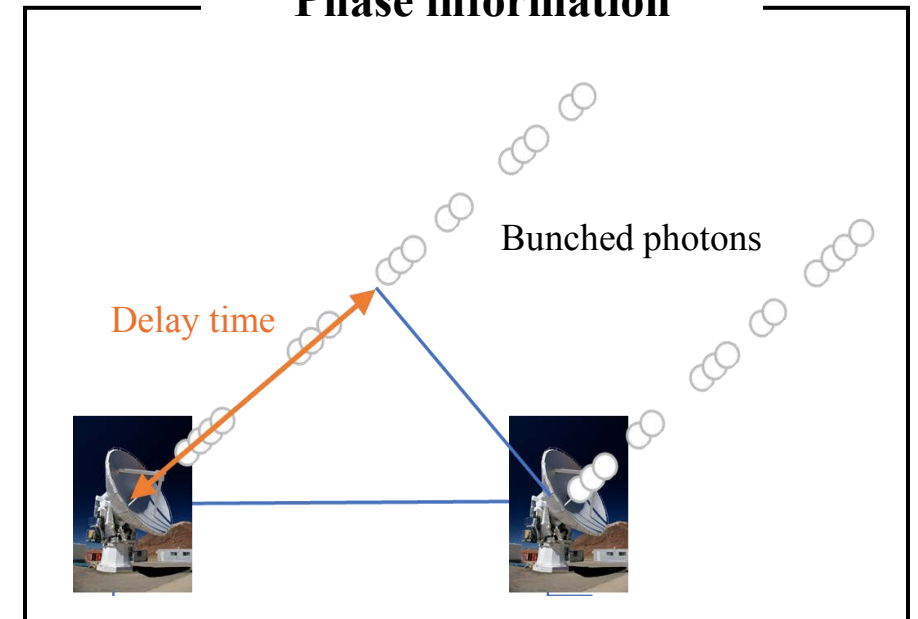
✓ Observable in space in the background noise limit

→ **Fast photon detectors (time resolution~1 ns) is required.**

Intensity correlation



Phase information



Research purpose

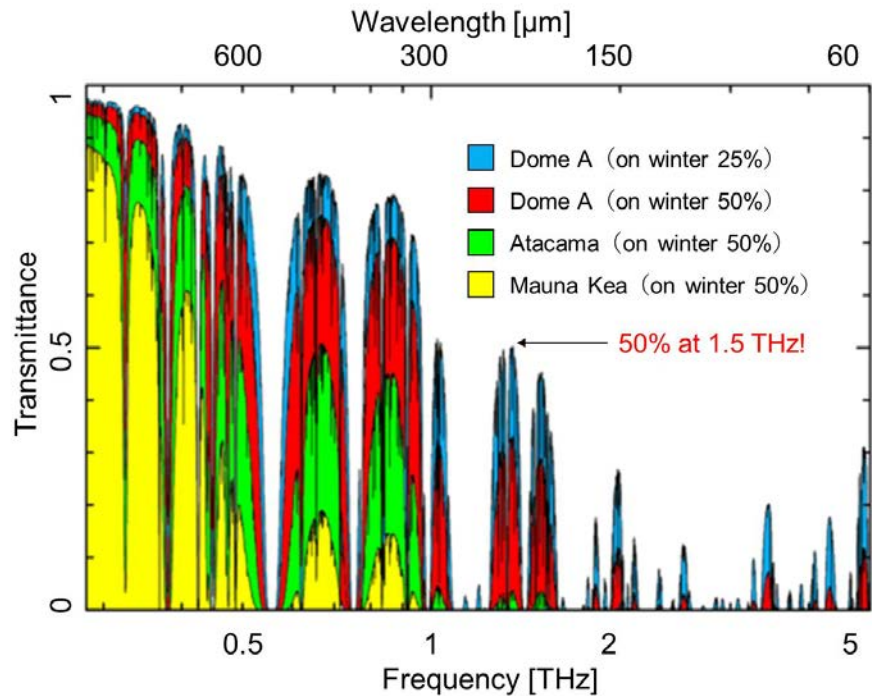
– 1.5 THz photon detectors for Antarctic experiments

The Antarctic terahertz window has high transmittance, compared to other sites.

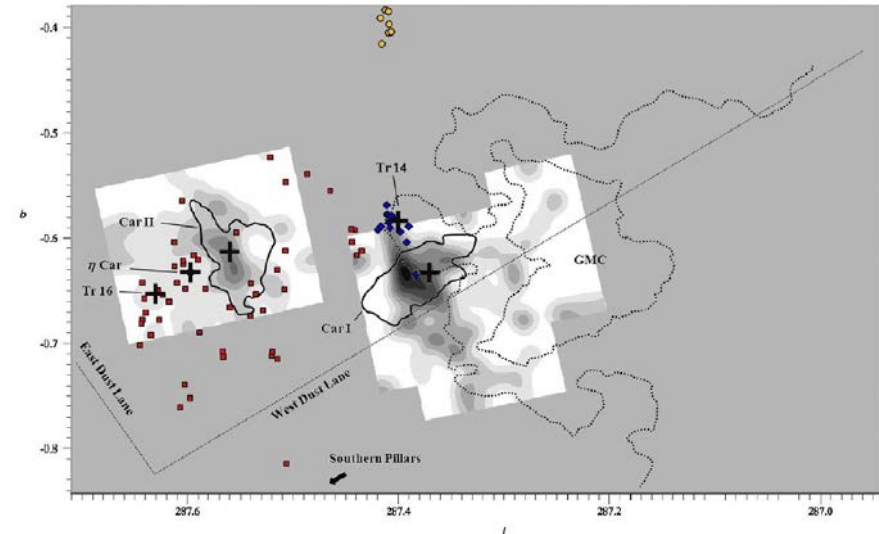
→ **We develop the 1.5 THz photon detectors for the Antarctic TH experiments (with two 30-cm telescopes).**

205 μm [NII] emission line is observed SPIFI on AST/RO, which has less angular resolution of $54''$.

→ **~ 10 m baseline interferometry exceeds the angular resolution of previous studies.**



Yang et al., 2010



Observed by SPIFI with 205 μm [NII]

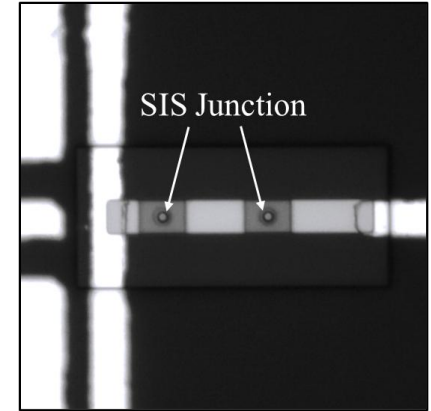
Oberst et al., 2011

Research background

– Our developments of SIS photon detectors for TII

□ Photon detectors with SIS (Superconductor-Insulator-Superconductor) junctions

- SIS is a Josephson junction with superconducting materials.
- SIS junctions can be work with fast photon detection process.
- Nb/Al-AlO_x/Al/Nb junctions which form resonance circuit to achieve required center frequency.



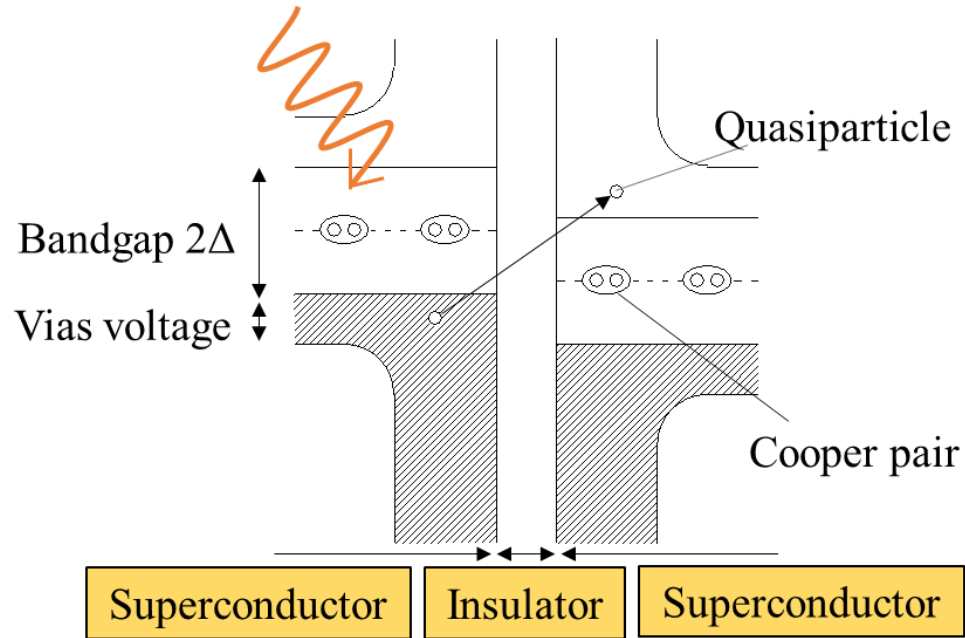
10 μm

660 GHz (Ezawa+2019, Ezawa+2020)	530 GHz (Ezawa+2024)	1.5 THz (Niwa+2024)
A photograph of a 660 GHz SIS junction device. It shows a long, thin, segmented strip on a substrate. A smaller inset image shows a close-up of the device's surface.	A schematic diagram and a micrograph of a 530 GHz SIS junction device. The schematic labels include "Twin-slot antenna", "CPW", and "GND plane". A scale bar indicates 100 μm. The micrograph shows the device with a 3 mm scale bar.	A photograph of a 1.5 THz SIS junction device. It features a central junction connected to a circular antenna structure. A smaller inset image shows a close-up of the junction area.

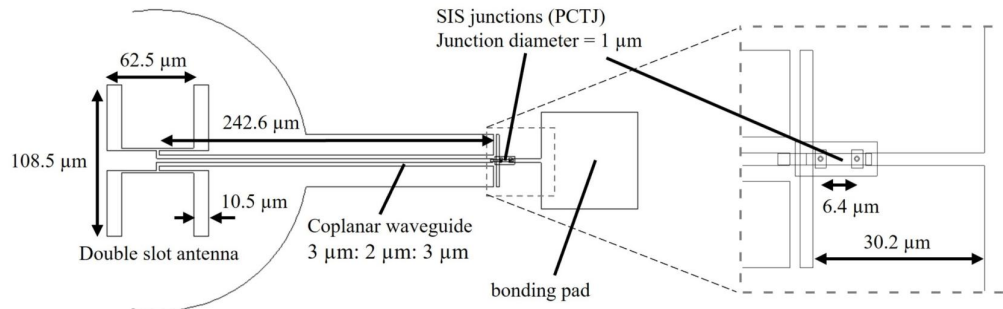
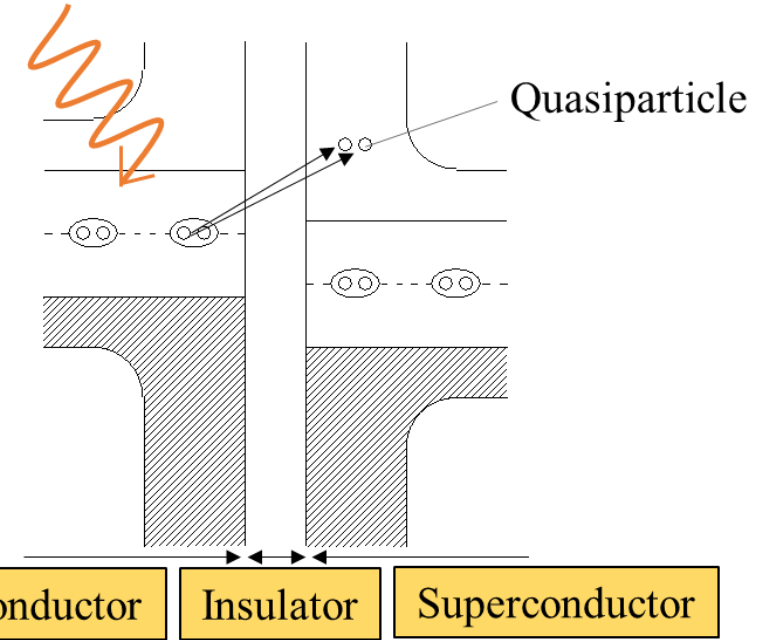
The design of 1.5 THz photon detectors

– Detection principle of antenna-coupled SIS for 1.5 THz photon

$2\Delta > h\nu$, Photon assisted tunneling



$2\Delta < h\nu$, Cooper pair breaking



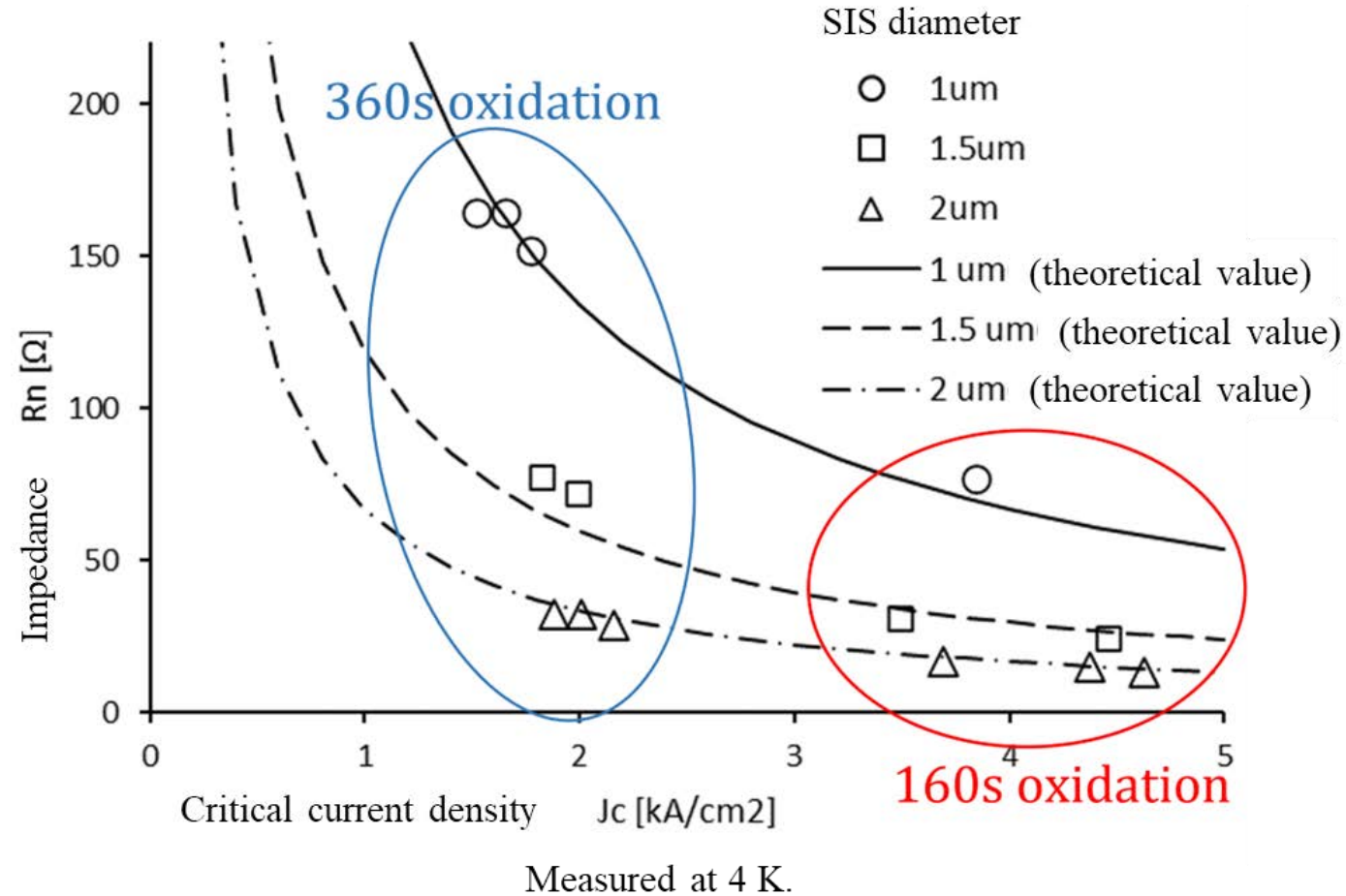
1.5 THz detectors
One photon \rightarrow Two quasiparticle

The design of 1.5 THz photon detectors

– Determination of SIS junction size

Leakage current of SIS oxidation film must be below 2 pA to identify single photon.

Smaller junction achieves extending bandwidth and low leakage current.



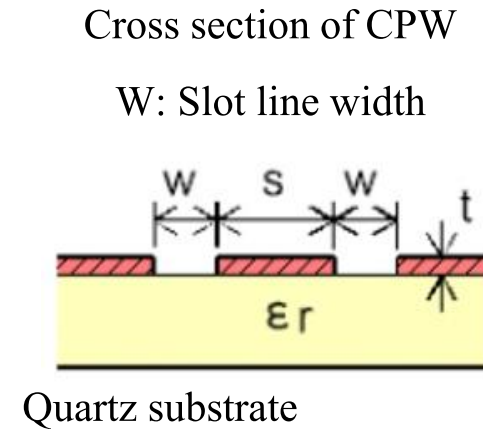
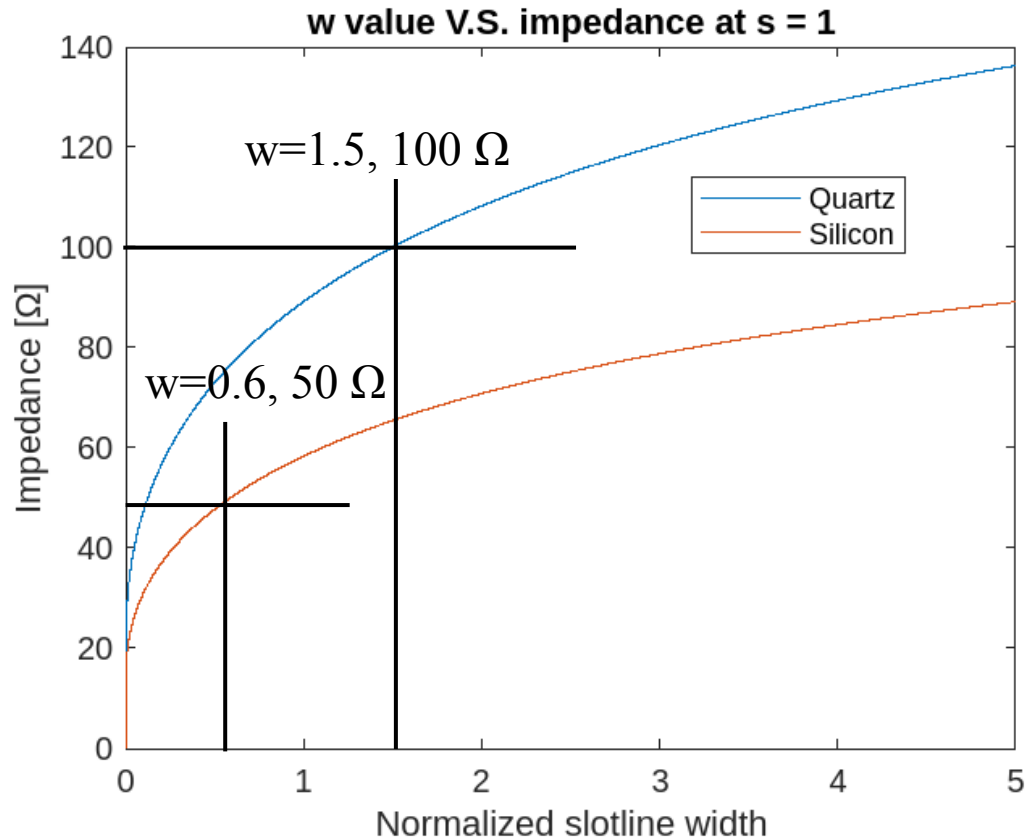
The design of 1.5 THz photon detectors

– Impedance tunings about CPW on Quartz wafer

Antenna, CPW, and SIS require impedance matching.

The fabrication facilities require a minimum slot line width to be wider than 1 μm .

→ Impedance of the CPW with the quartz substrate $\epsilon_r = 4.456$ calculated in MATLAB (Mathworks).



The design of 1.5 THz photon detectors

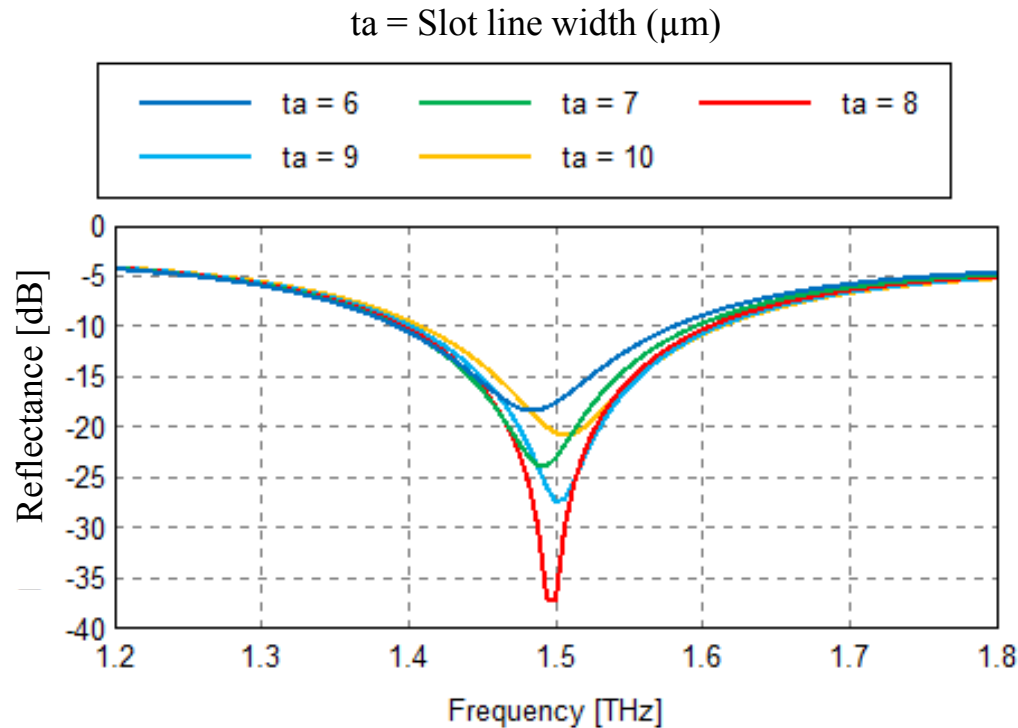
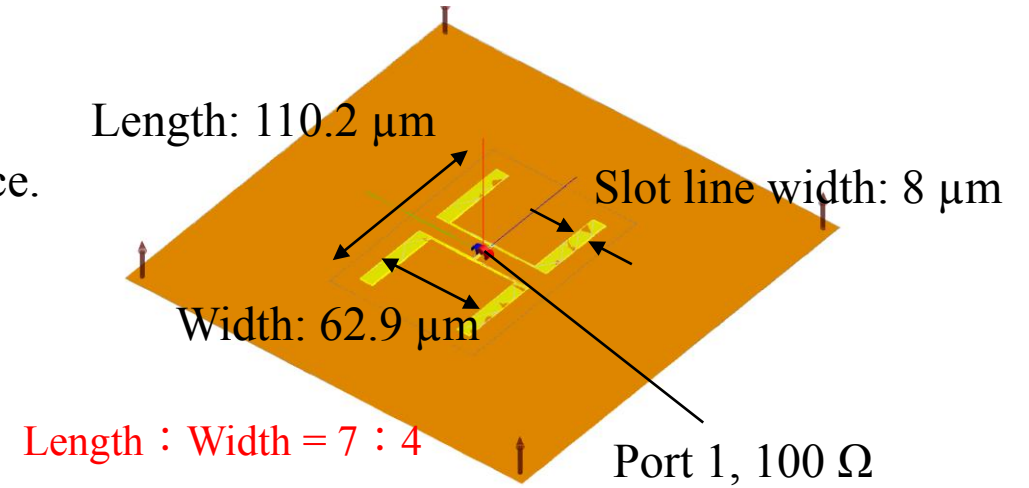
– Electromagnetic calculations of double slot antenna

Length and width: Larger effect on resonance frequency than on impedance.

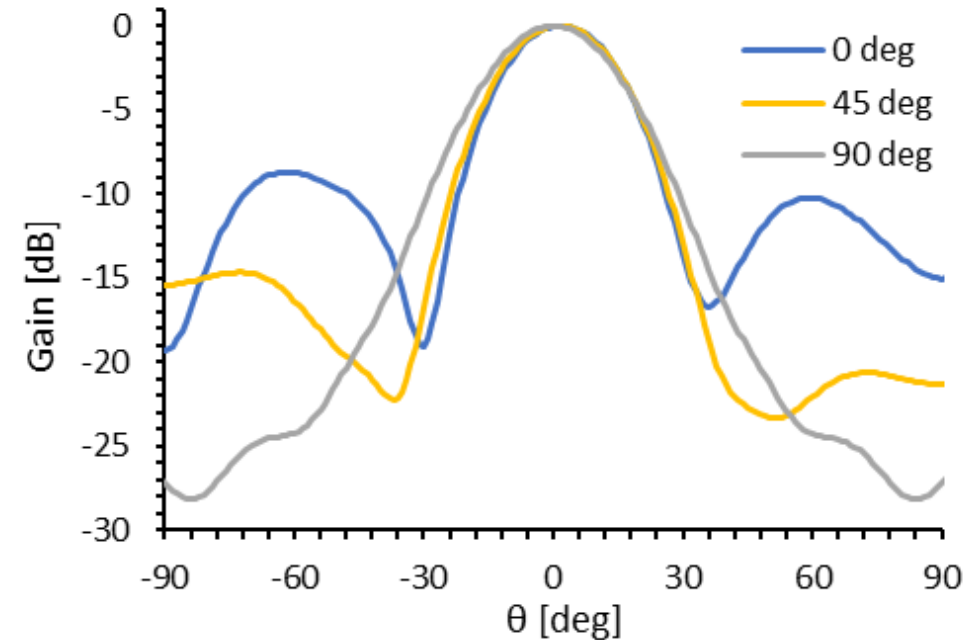
Note that the aspect ratio affects beam shape distortion.

Following the 7:4 aspect ratio of a previous study (Filipovic et al., 1953)

Slot line width: Larger effect on impedance than resonant frequency.



Antenna reflectance (Calculated with FEKO).



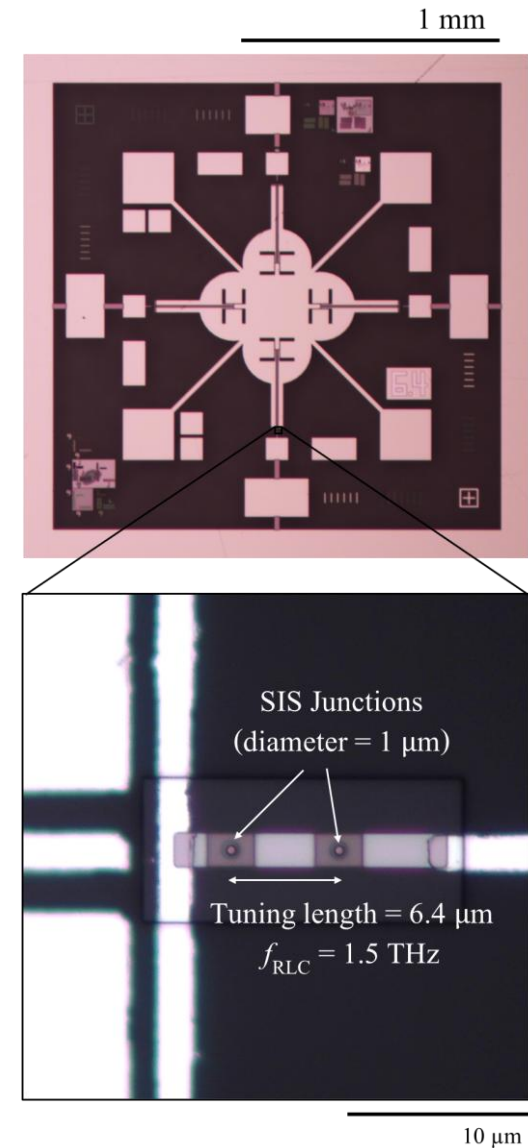
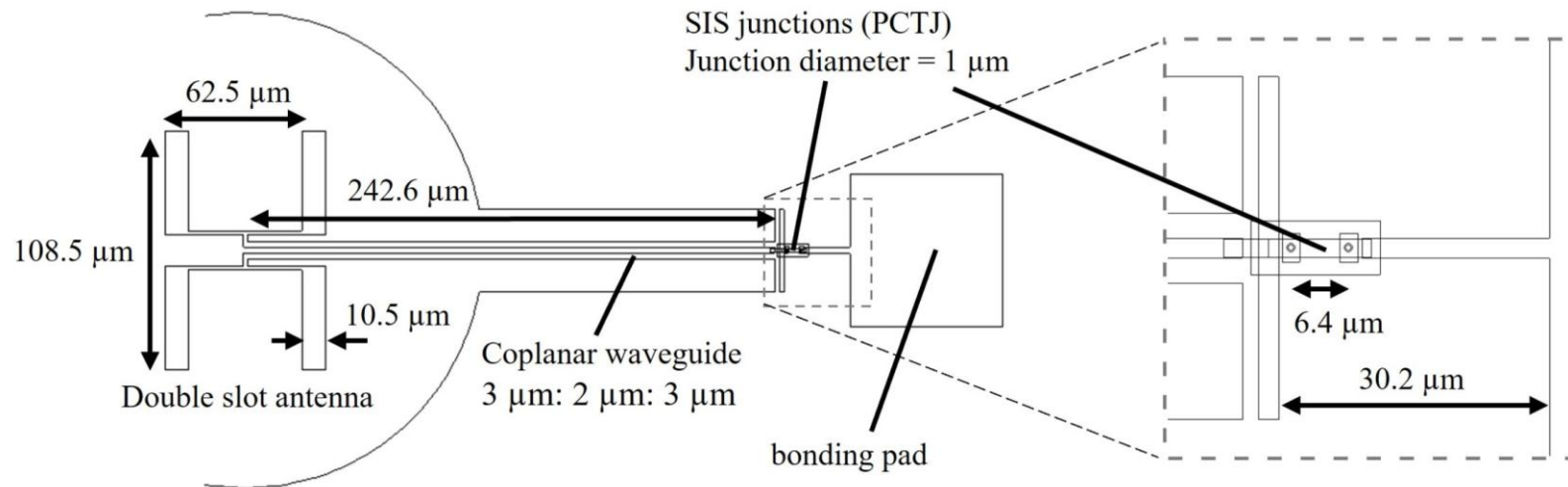
Antenna beam pattern at 1.5 THz (Calculated with HFSS).

The design of 1.5 THz photon detectors

– Schematics of the detectors and fabricated detectors

We designed and fabricated the detectors.

- Fabrication facility: ATC clean room in NAOJ
- Fabrication terms: 1~3 months



Evaluations of 1.5 THz photon detectors

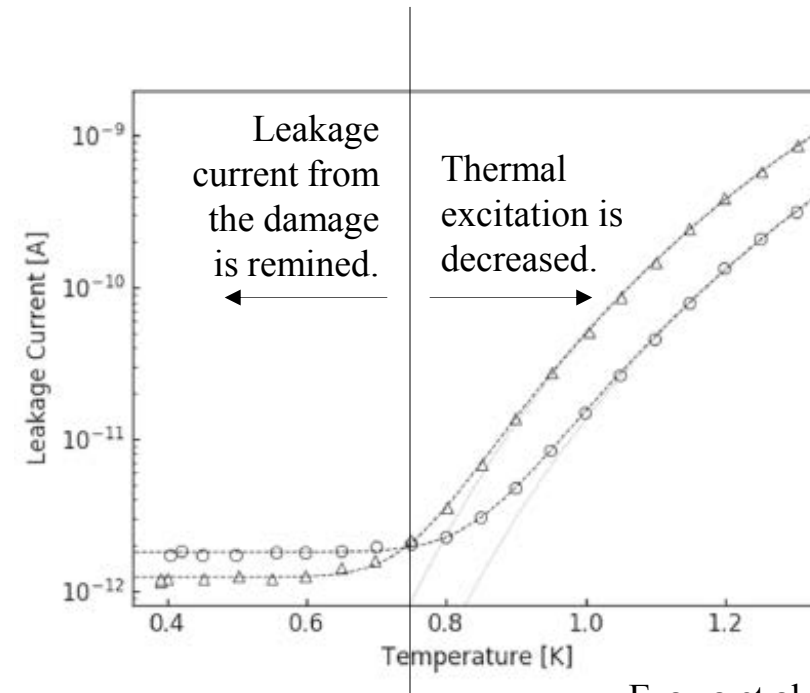
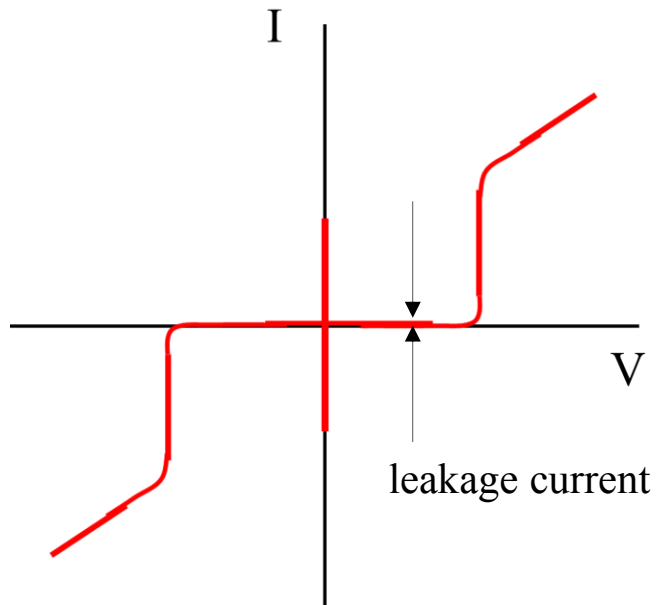
– IV characteristics and leakage current

Low leakage current* is preferred for the 1.5 THz photon detectors.

*Leakage current: one of the current noise for the SIS caused by thermal excitation and damage of the insulator in the SIS junctions.

Under 240 K background radiation, **the 1.5 THz photon detectors require the leakage current to be below 2.5 nA.**

We clarified that leakage current caused by thermal excitation is suppressed at below 0.8 K.



Ezawa et al., 2020

Low speed readout circuits at low temperature

– Design of the circuit

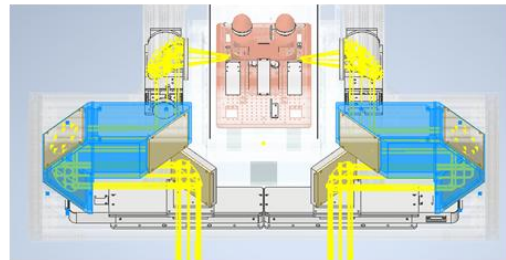
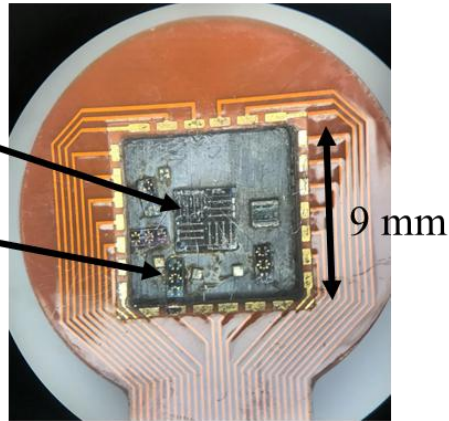
Capacitance between SIS and current amplifier inhibits high-speed readout.

GaAs-JFET can operate at low temperature ≈ 0.8 K and be placed at a few millimeters next to SIS.

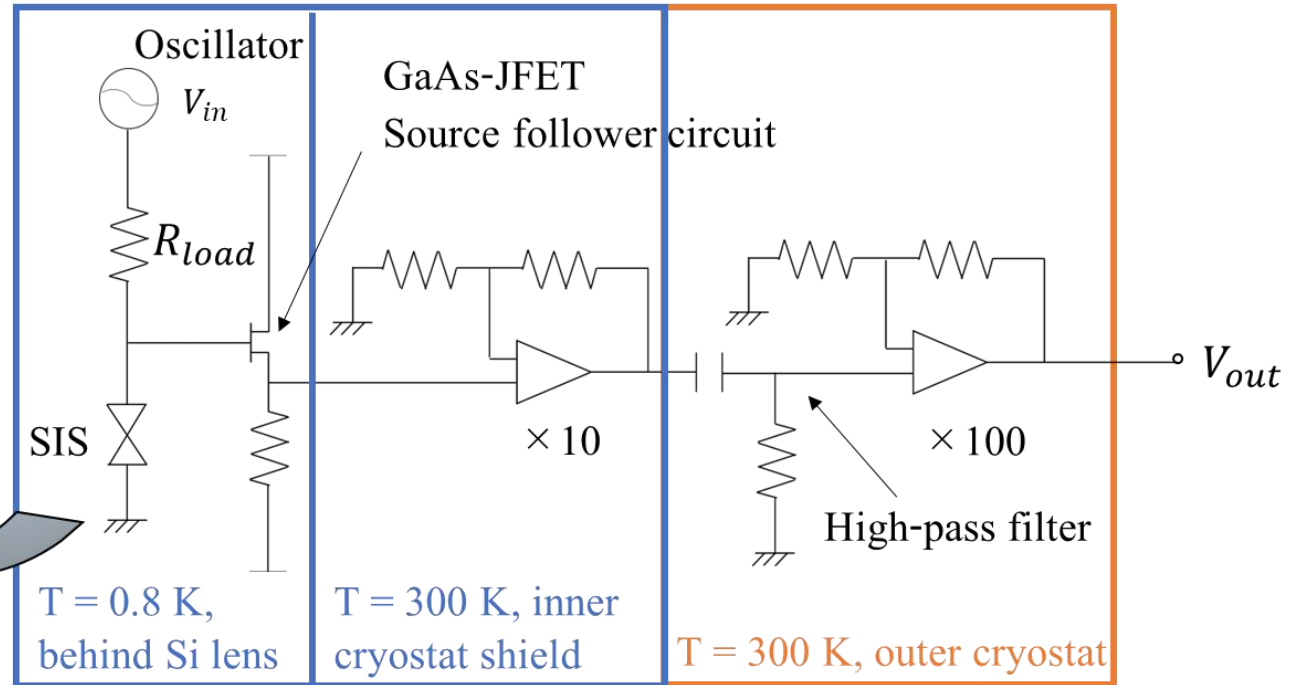
$$V = \frac{V_{out}}{G}, \quad I = \frac{V_{in} - V}{R_{load}}$$

660 GHz SIS photon detector chip

GaAs-JFET chip



Cryostat image, LTD20, MP-057

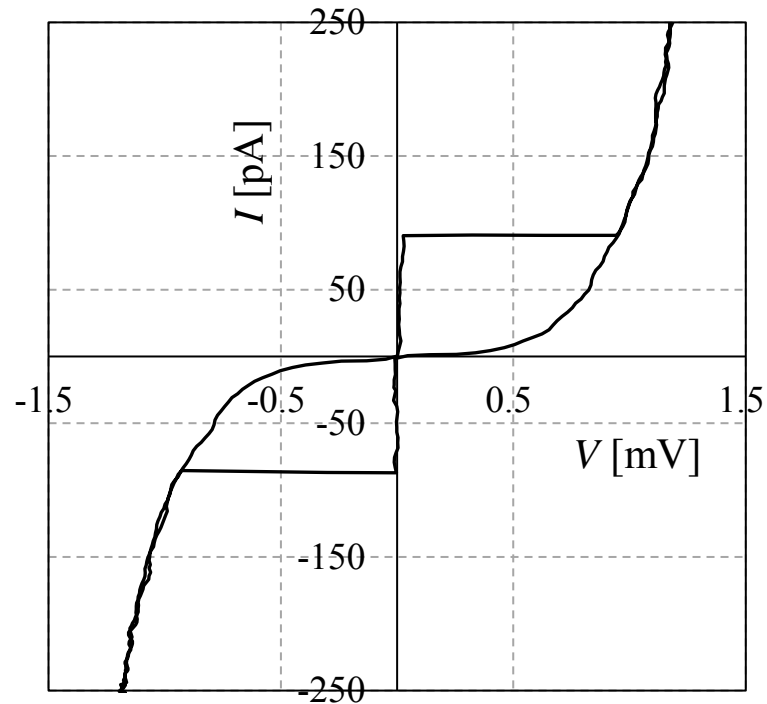


Low speed readout circuits at 0.8 K

– Evaluation of the circuit with 660 GHz photon detectors

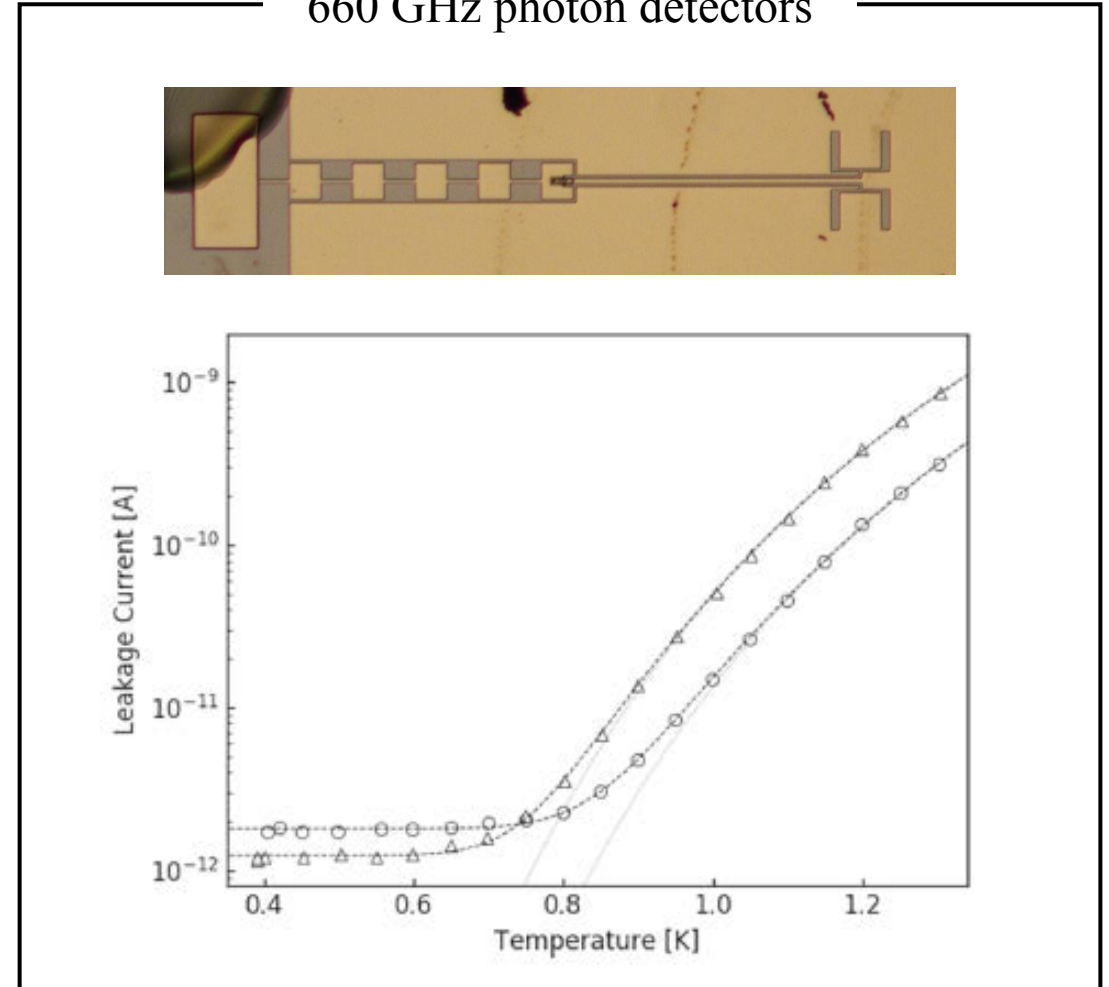
The leakage current is 15 pA@0.6 mV at 0.8 K.

This result is nearly consistent our previous measurement with filter (no AR) + liq. He4 dewar (3pA@0.6mV at 0.8 K).



IV characteristics at 0.8 K

660 GHz photon detectors

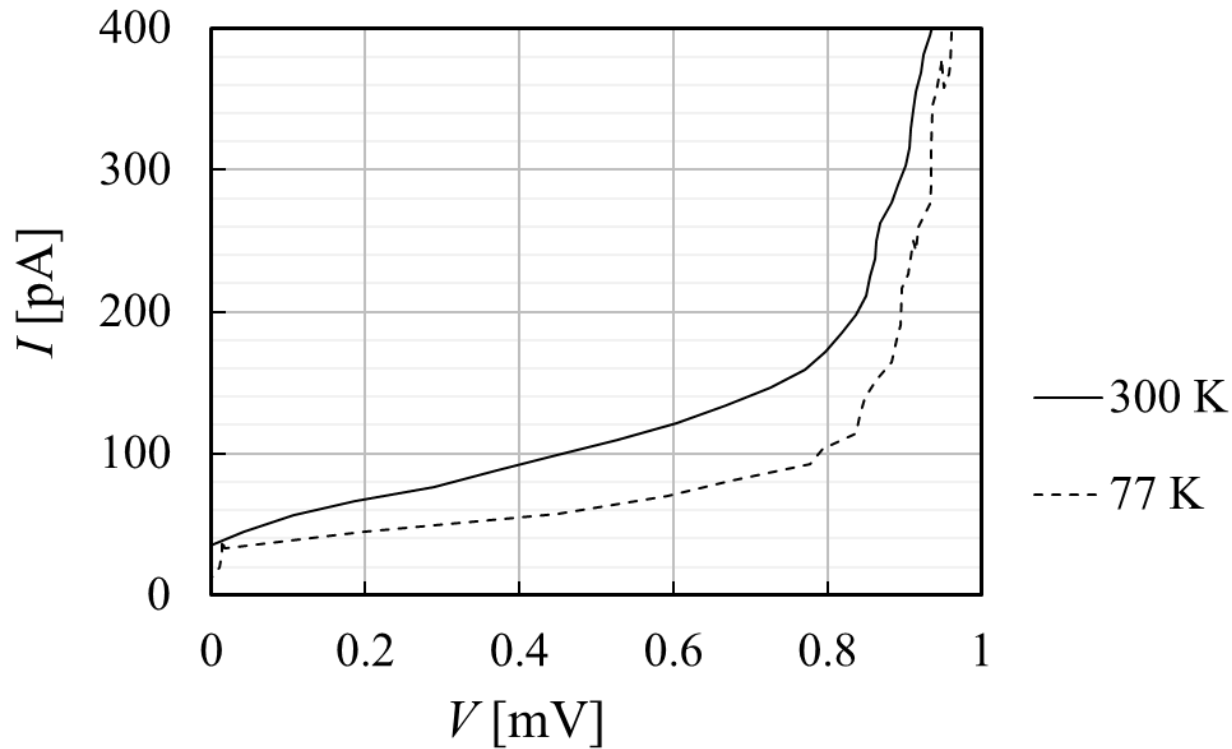


Low speed readout circuits at 0.8 K

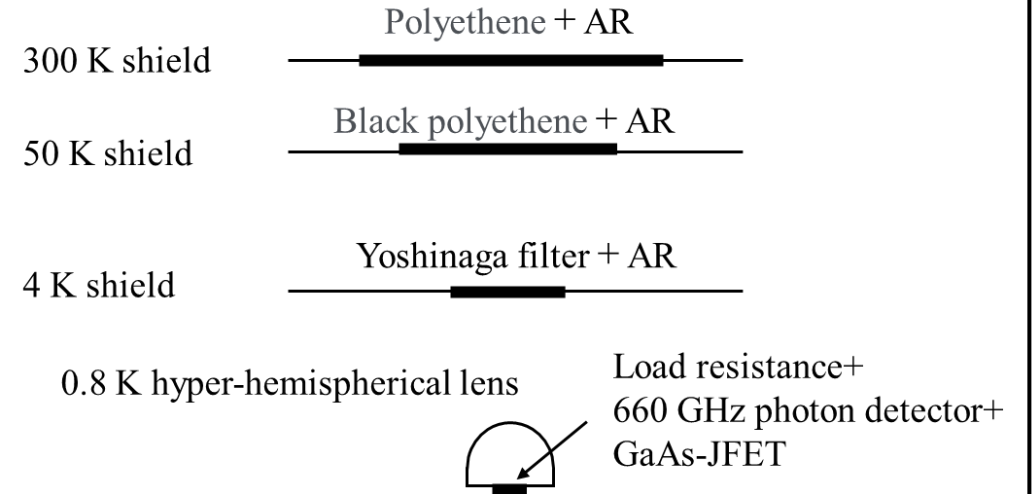
– Evaluation of the circuit with 660 GHz photon detectors

Optical efficiency $\eta=0.12\%$.

This result is worse than our previous measurement with filter (no AR) + liq. He4 dewar ($\eta=1.3\%$).

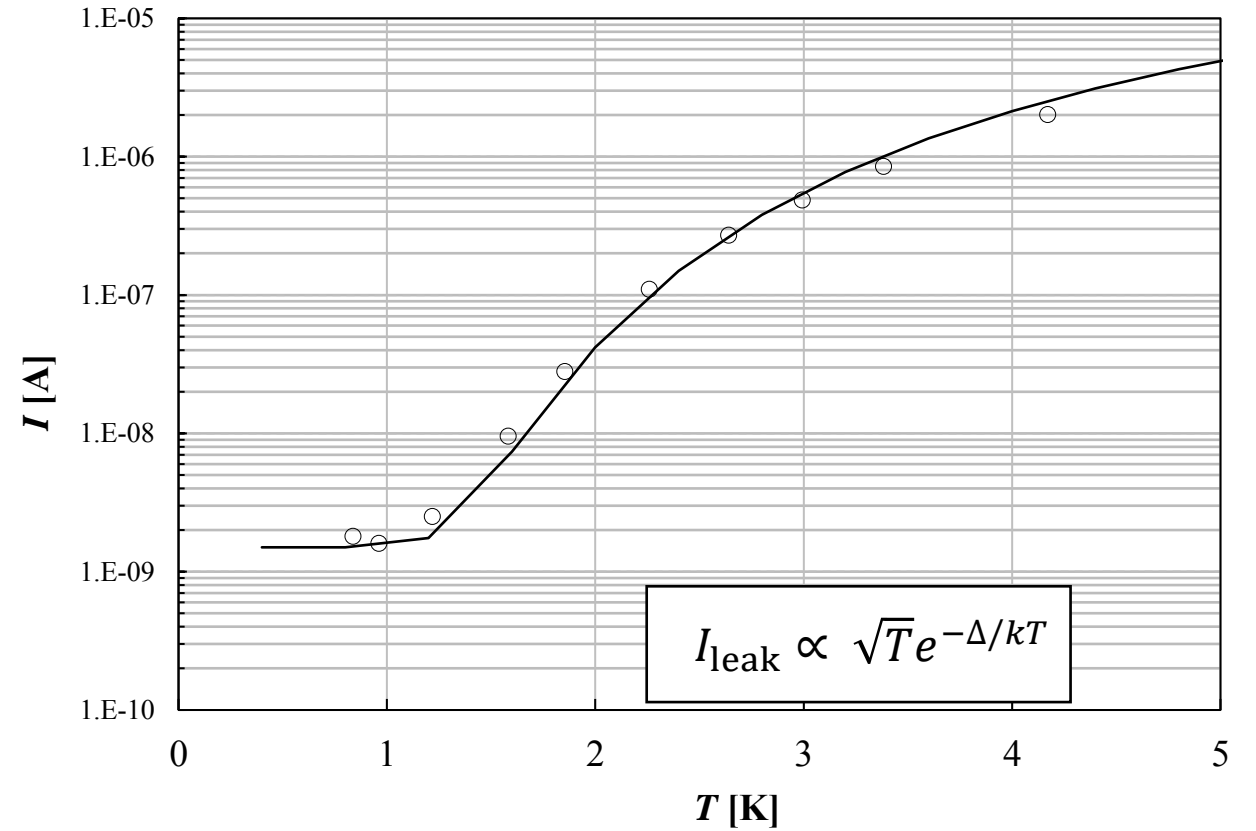
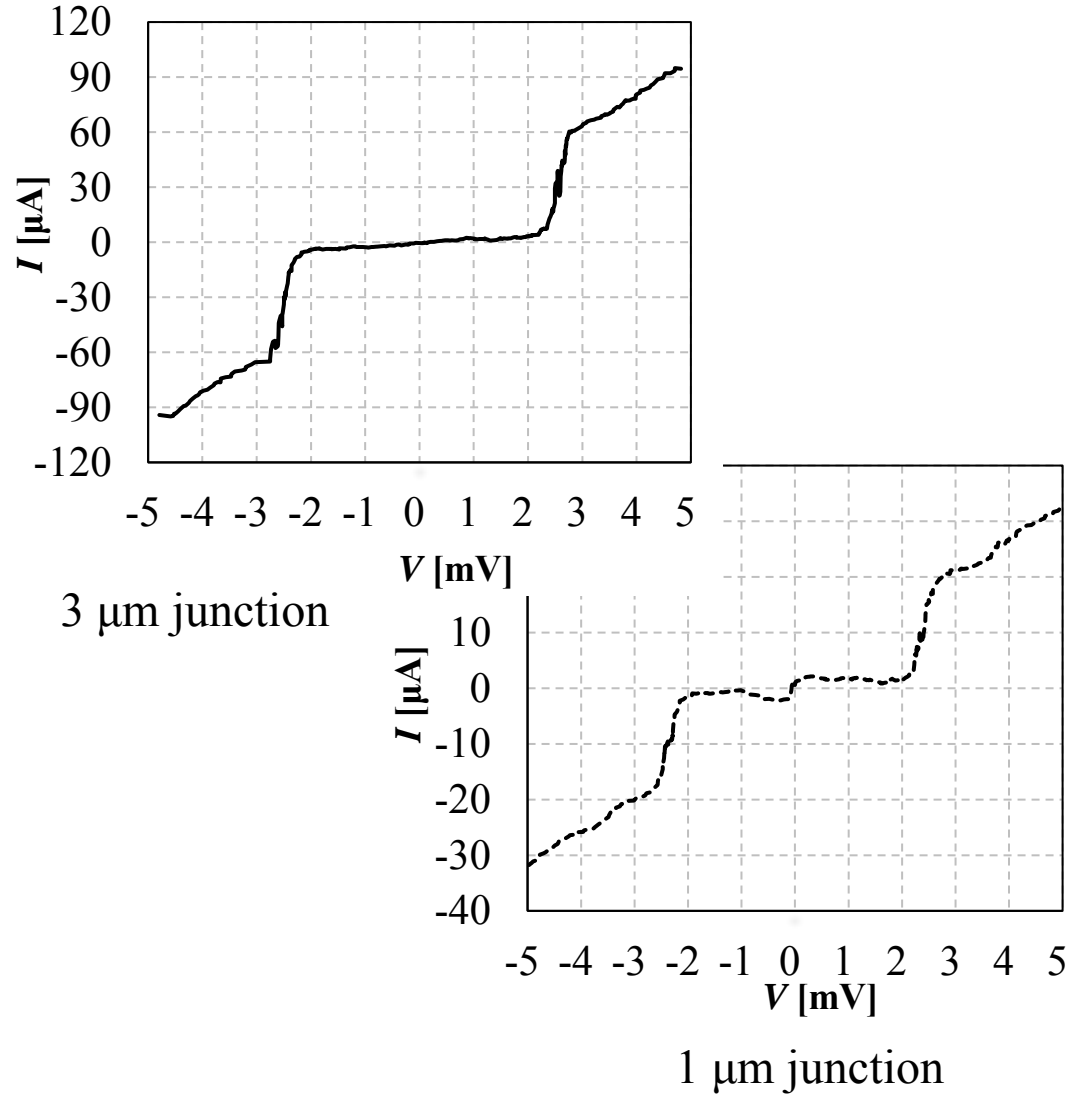


Measurement setup



Evaluations of 1.5 THz photon detectors

– IV characteristics at low temperature



Temperature v.s. Leakage current of 3 μm junction
The solid line shows BCS model.

Summary and Future works

We are developing 1.5 THz photon detectors to use for the Antarctic TII experiment.

- I-V characteristics measurements at 4 K

 - The fabricated detectors show reasonable I-V characteristics.

 - However, the performance is not ideal and needs more fabrication parameter tuning.

- Low speed readout circuits is developed and evaluated at low temperature.

We will continue the following developments:

- The evaluation of the 1.5 THz photon detectors

- Iterate fabrication to reduce the leakage current and to optimize critical current density

- (Additional option) Set up an experimental system with optical fibers for pulse input

 - We measure the time resolution of 660 GHz photon detector for the first time.